

36. The method of fabricating a thin film transistor according to claim 33, wherein at least a negative electrode and a positive electrode are formed prior to the crystallizing step, and crystallization of the amorphous silicon layer occurs faster at the negative electrode than at the positive electrode. - -

REMARKS

New Claims 25-36 have been added.

Claim 21 was objected to because of a typographical error. The claim has been amended to correct the error. Withdrawal of the objection is respectfully requested.

Claims 11 and 12 stand rejected under 35 U.S.C. § 112. This rejection is traversed with respect to the claims as amended. The claims have been amended to recite that the electrodes are formed prior to crystallization. Withdrawal of the rejection with respect to the claims as amended is respectfully requested.

Claim 23 stands rejected under 35 U.S.C. § 112. This rejection is traversed with respect to the claim as amended. Claim 23 has been amended to provide sufficient antecedent basis for the first electrode and the second electrode. Withdrawal of the rejection with respect to the claims as amended is respectfully requested.

Claims 1-24 stand rejected under 35 U.S.C. § 103 in view of Song et al. This rejection is traversed. Submitted herewith is a Declaration under 37 C.F.R. § 1.131 that establishes that the Applicant is the sole inventor and that the other authors listed in the article were merely working under the Applicant's direction. This declaration is sufficient to remove Song et al. as a reference pursuant to M.P.E.P. § 715.01(c). Withdrawal of the rejection is respectfully requested.

In view of the foregoing remarks, all claims are believed to be in condition for immediate

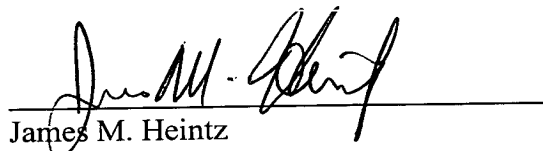
allowance. Allowance of the application is respectfully solicited.

Respectfully submitted,

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